

S11	109662	field effect transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 13:25
S12	1	S11 and (channel region) and (plurality semiconductive region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 13:28
S13	13553	S11 and (channel region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 13:32
S14	0	S13 and (plurality near\$4 region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 13:30
S15	6135	S13 and plurality	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 13:30
S16	919	S13 and (self align\$4 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 13:57
S17	193	S13 and ((self align\$4 gate) near3 (source drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 14:01
S18	22	S13 and ((self align\$4 gate) near3 (source drain)) and emitter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 14:51
S19	0	S18 and polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 14:49
S20	0	S13 and ((self align\$4 gate) near3 (source drain)) and (plurality emitter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 14:51

S21	78	S17 and ((self align\$4 gate) near3 (source drain)) and plurality	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 15:52
S22	14	S18 and ((self align\$4 gate) near3 (source drain)) and plurality	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 14:53
S23	0	S17 and ((self align\$4 gate) near3 (source drain)) and (control\$4 current) and (control emiss\$4 electrons)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 15:59
S24	0	S17 and ((self align\$4 gate) near3 (source drain)) and (control emiss\$4 electrons)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 15:53
S25	0	S17 and ((self align\$4 gate) near3 (source drain)) and (emiss\$4 electrons)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 15:54
S26	6	S17 and ((self align\$4 gate) near3 (source drain)) and emiss\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 15:54
S27	3	S13 and (control\$4 current) and (control emiss\$4 electrons)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/09 16:41
S28	527	S13 and (gate with polis\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 16:02
S29	5	S21 and (gate with polis\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 16:25
S30	5	S17 and (gate with polis\$4 with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2004/12/08 16:26